

#### **FEATURES**

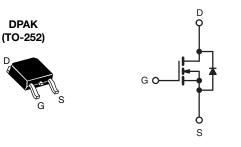
- Low Figure-of-Merit (FOM) Ron x Qg
- Low Input Capacitance (Ciss)
- Reduced Switching and Conduction Losses
- Ultra Low Gate Charge (Q<sub>q</sub>)
- Avalanche Energy Rated (UIS)
- Material categorization: For definitions of compliance please see www.freescale.net.cn

#### **APPLICATIONS**

- Server and Telecom Power Supplies
- Switch Mode Power Supplies (SMPS)
- Power Factor Correction Power Supplies (PFC)
- Lighting
  - High-Intensity Discharge (HID)
  - Fluorescent Ballast Lighting
- Industrial
  - Welding
  - Induction Heating
  - Motor Drives
  - Battery Chargers
  - Renewable Energy
  - Solar (PV Inverters)

PRODUCT SUMMA	RY	
V <sub>DS</sub> (V) at T <sub>J</sub> max.	650	)
$R_{DS(on)}$ max. at 25 °C ( $\Omega$ )	V <sub>GS</sub> = 10 V	0.6
Q <sub>g</sub> max. (nC)	40	
Q <sub>gs</sub> (nC)	5	
Q <sub>gd</sub> (nC)	9	
Configuration	Sing	le





N-Channel MOSFET

ORDERING INFORMATION	
Package	DPAK (TO-252)
	SiHD7N60E-GE3
Load (Dh) from and Hologon from	SiHD7N60ET-GE3
Lead (Pb)-free and Halogen-free	SiHD7N60ETR-GE3
	SiHD7N60ETL-GE3

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			$V_{DS}$	600	
Gate-Source Voltage			V	± 20	V
Gate-Source Voltage AC (f > 1 Hz)			$V_{GS}$	30	
Continuous Drain Current (T, I = 150 °C)	V <sub>GS</sub> at 10 \	$T_{\rm C} = 25  ^{\circ}{\rm C}$ $T_{\rm C} = 100  ^{\circ}{\rm C}$	I-	7	
Continuous Drain Current (1) = 130 °C)	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 100 °C	I <sub>D</sub>	5	А
Pulsed Drain Current <sup>a</sup>			I <sub>DM</sub>	18	
Linear Derating Factor				0.63	W/°C
Single Pulse Avalanche Energy <sup>b</sup>		E <sub>AS</sub>	43	mJ	
Maximum Power Dissipation			P <sub>D</sub>	78	W
Operating Junction and Storage Temperature Range			T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 150	°C
Drain-Source Voltage Slope	T <sub>J</sub> =	: 125 °C	dV/dt	37	V/ns
Reverse Diode dV/dt <sup>d</sup>			αν/αι	3	V/IIS
Soldering Recommendations (Peak Temperatu	ure) fo	r 10 s		300°	°C

#### Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature.
- b.  $V_{DD} = 50 \text{ V}$ , starting  $T_J = 25 \text{ °C}$ , L = 13.8 mH,  $R_g = 25 \Omega$ ,  $I_{AS} = 2.5 \text{ A}$ .
- c. 1.6 mm from case.
- d.  $I_{SD} \le I_D$ , dI/dt = 100 A/ $\mu$ s, starting  $T_J = 25$  °C.



THERMAL RESISTANCE RATI	NGS			
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R <sub>thJA</sub>	-	62	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	1.6	G/ VV

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static		1					
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$		600	-	-	V
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	Referenc	e to 25 °C, I <sub>D</sub> = 1 mA	i	0.68	-	V/°C
Gate-Source Threshold Voltage (N)	V <sub>GS(th)</sub>	V <sub>DS</sub> :	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2	-	4	V
Gate-Source Leakage	I <sub>GSS</sub>		V <sub>GS</sub> = ± 20 V	1	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		$V_{DS} = 600 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 \text{ °C}$		-	1 10	μA
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS} = 400 \text{ V}$	$I_D = 3.5 \text{ A}$	-	0.5	0.6	Ω
Forward Transconductance	9fs		= 50 V, I <sub>D</sub> = 3.5 A	-	1.9	-	S
Dynamic	915	- 55			1	<u>I</u>	
Input Capacitance	C <sub>iss</sub>	T		_	680	T _	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V},$ $V_{DS} = 100 \text{ V},$ f = 1  MHz		-	39	-	pF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	5	-	
Effective Output Capacitance, Energy Related <sup>a</sup>	C <sub>o(er)</sub>	- V <sub>DS</sub> = 0 V to 480 V, V <sub>GS</sub> = 0 V		-	34	-	
Effective Output Capacitance, Time Related <sup>b</sup>	$C_{o(tr)}$			-	100	-	
Total Gate Charge	Qg			-	20	40	
Gate-Source Charge	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$I_D = 3.5 \text{ A}, V_{DS} = 480 \text{ V}$	-	5	-	nC
Gate-Drain Charge	$Q_{gd}$			ı	9	-	
Turn-On Delay Time	t <sub>d(on)</sub>			-	13	26	
Rise Time	t <sub>r</sub>	$V_{DD} = 480 \text{ V}, I_{D} = 3.5 \text{ A}, V_{GS} = 10 \text{ V}, R_{g} = 9.1 \Omega$		-	13	26	ns
Turn-Off Delay Time	t <sub>d(off)</sub>			-	24	48	
Fall Time	t <sub>f</sub>			1	14	28	
Gate Input Resistance	R <sub>g</sub>	f = 1 MHz, open drain		-	1.1	-	Ω
<b>Drain-Source Body Diode Characteristic</b>	s						
Continuous Source-Drain Diode Current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode		-	-	7	
Pulsed Diode Forward Current	I <sub>SM</sub>			-	-	28	A
Diode Forward Voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 3.5 A, V <sub>GS</sub> = 0 V		-	-	1.2	V
Reverse Recovery Time	t <sub>rr</sub>			-	230	-	ns
Reverse Recovery Charge	Q <sub>rr</sub>	$T_J = 25 \text{ °C}, I_F = I_S = 3.5 \text{ A},$ $dI/dt = 100 \text{ A/µs}, V_R = 20 \text{ V}$		-	1.9	-	μC
Reverse Recovery Current	I <sub>RRM</sub>			_	14	_	Α

#### Notes

- a.  $C_{oss(er)}$  is a fixed capacitance that gives the same energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ . b.  $C_{oss(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 % to 80 %  $V_{DSS}$ .



#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

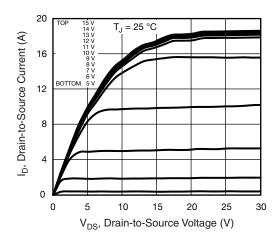


Fig. 1 - Typical Output Characteristics

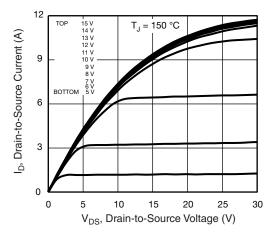


Fig. 2 - Typical Output Characteristics

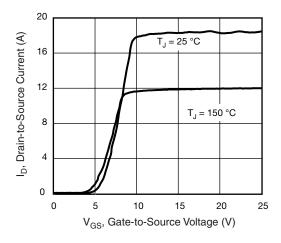


Fig. 3 - Typical Transfer Characteristics

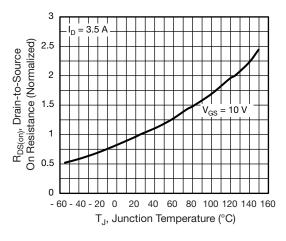


Fig. 4 - Normalized On-Resistance vs. Temperature

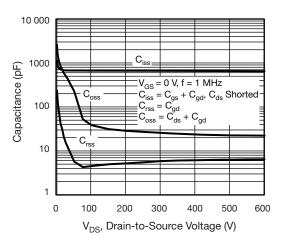


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

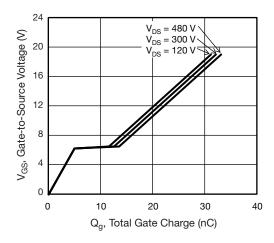


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



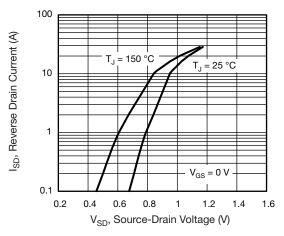


Fig. 7 - Typical Source-Drain Diode Forward Voltage

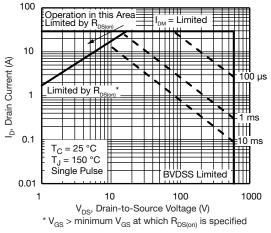


Fig. 8 - Maximum Safe Operating Area

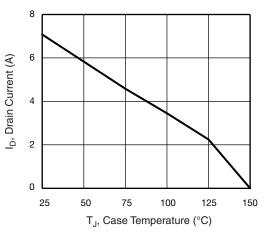


Fig. 9 - Maximum Drain Current vs. Case Temperature

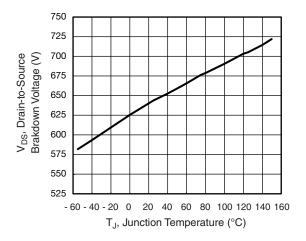


Fig. 10 - Temperature vs. Drain-to-Source Voltage

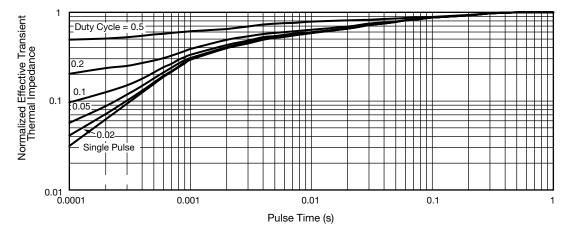


Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case



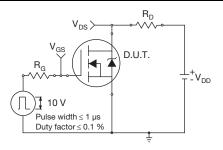


Fig. 12 - Switching Time Test Circuit

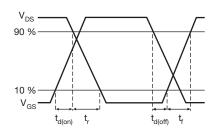


Fig. 13 - Switching Time Waveforms

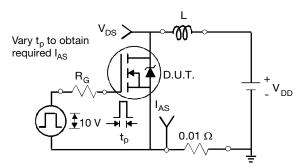


Fig. 14 - Unclamped Inductive Test Circuit

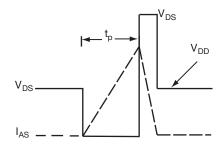


Fig. 15 - Unclamped Inductive Waveforms

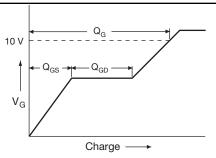


Fig. 16 - Basic Gate Charge Waveform

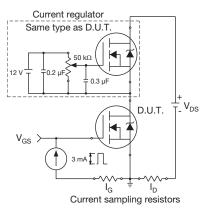
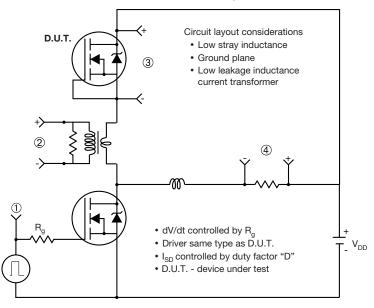


Fig. 17 - Gate Charge Test Circuit



#### Peak Diode Recovery dV/dt Test Circuit



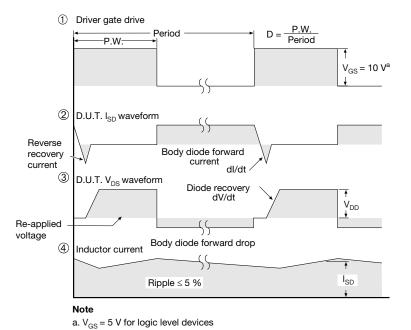
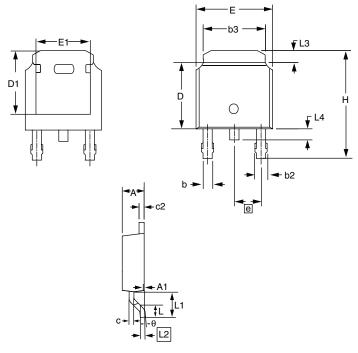


Fig. 18 - For N-Channel



#### **TO-252AA (HIGH VOLTAGE)**



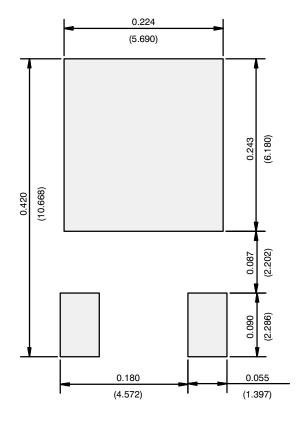
	MILLI	METERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Е	6.40	6.73	0.252	0.265	
L	1.40	1.77	0.055	0.070	
L1	2.74	2.743 REF		0.108 REF	
L2	0.50	8 BSC	0.020 BSC		
L3	0.89	1.27	0.035	0.050	
L4	0.64	1.01	0.025	0.040	
D	6.00	6.22	0.236	0.245	
Н	9.40	10.40	0.370	0.409	
b	0.64	0.88	0.025	0.035	
b2	0.77	1.14	0.030	0.045	
b3	5.21	5.46	0.205	0.215	
е	2.28	2.286 BSC		0.090 BSC	
Α	2.20	2.38	0.087	0.094	
A1	0.00	0.13	0.000	0.005	
С	0.45	0.60	0.018	0.024	
c2	0.45	0.58	0.018	0.023	
D1	5.30	-	0.209	-	
E1	4.40	-	0.173	-	
θ	0,	10'	0'	10'	

ECN: S-81965-Rev. A, 15-Sep-08 DWG: 5973

#### Notes

- 1. Package body sizes exclude mold flash, protrusion or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 0.10 mm per side.
- 2. Package body sizes determined at the outermost extremes of the plastic body exclusive of mold flash, gate burrs and interlead flash, but including any mismatch between the top and bottom of the plastic body.
- 3. The package top may be smaller than the package bottom.
- 4. Dimension "b" does not include dambar protrusion. Allowable dambar protrusion shall be 0.10 mm total in excess of "b" dimension at maximum material condition. The dambar cannot be located on the lower radius of the foot.

#### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



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